

Do Not  
Enter  
7/10/2004  
M>

**Amendments to the Claims:**

Please amend Claims 1, 6, 14, 17, 19, and 22 as indicated in the following listing of claims, which replaces all prior versions, and listings, of claims in the application.

**Listing of Claims:**

1. (Currently Amended) A method for depositing a film on a substrate wafer disposed within a process chamber, the method comprising:
  - providing a first gaseous mixture to the process chamber;
  - inductively generating a plasma from the first gaseous mixture with a toroidal plasma source disposed within the process chamber to deposit a first portion of the film on the substrate wafer, the toroidal plasma source being disposed within the process chamber and comprising a core and a coil;
  - thereafter, flowing an etchant gas into the process chamber without terminating the plasma to provide a net etching back of part of the first portion of the film; and
  - thereafter, providing a second gaseous mixture to the process chamber without terminating the plasma to deposit a second portion of the film on the substrate wafer.
2. (Original) The method recited in claim 1 further comprising applying an electrical bias to the substrate while flowing the etchant gas.
3. (Original) The method recited in claim 2 wherein the bias has a power density approximately between 0.9 W/cm<sup>2</sup> and 3.2 W/cm<sup>2</sup>.
4. (Original) The method recited in claim 1 wherein the second gaseous mixture is substantially the same as the first gaseous mixture.